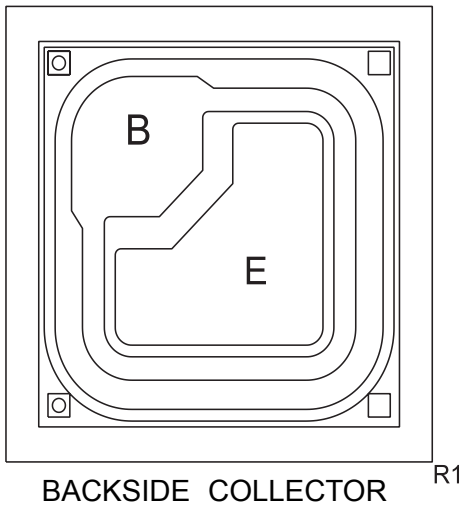


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	15 x 15 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	4.0 x 4.0 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

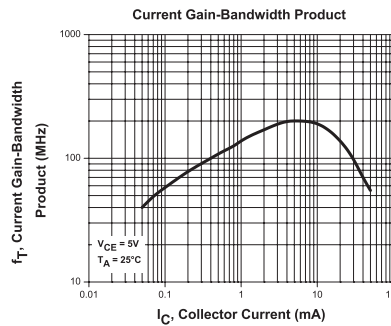
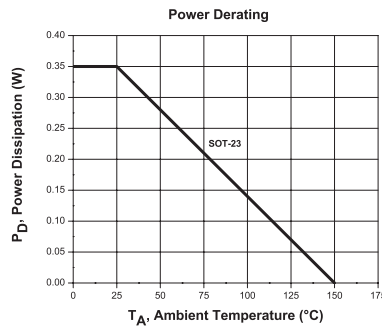
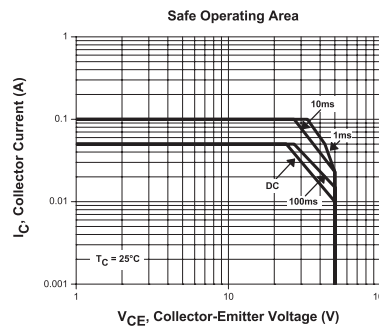
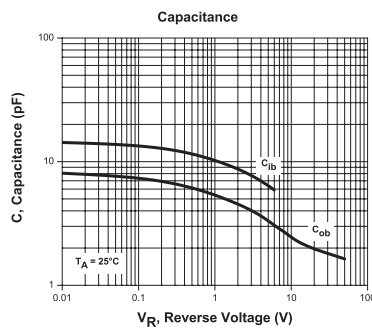
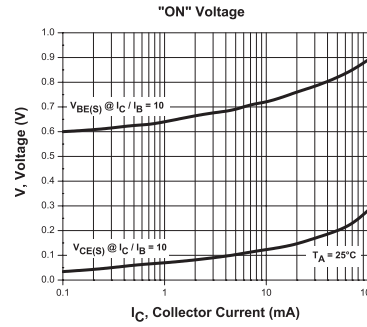
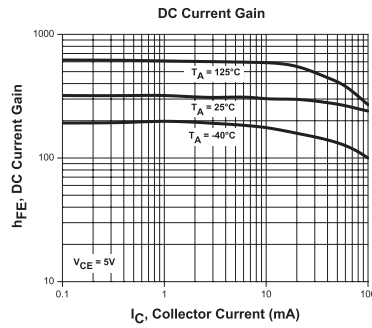
53,730

**PRINCIPAL DEVICE TYPES**

2N2605  
2N3799  
PN4250A  
CMPT5086  
CMPT5087

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R3 (21-August 2006)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R3 (21-August 2006)